**Product data sheet** 

## 1. General description

Dual ultrafast power diode in a SOT429 (3-lead TO-247) plastic package.

### 2. Features and benefits

- Very low on-state loss
- Fast switching
- Soft recovery characteristic minimizes power consuming oscillations
- High thermal cycling performance
- Low thermal resistance

# 3. Applications

Output rectifiers in high-frequency switched-mode power supplies

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage			-	-	400	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 104 °C; square-wave pulse; per diode; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>		-	-	15	А
I <sub>O(AV)</sub>	average output current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 94 °C; square-wave pulse; both diodes conducting		-	-	30	A
Static characte	eristics		,				,
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	0.95	1.12	V
Dynamic characteristics							
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7		-	35	60	ns





**Dual ultrafast power diode** 

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		A1 A2
2	K	cathode		
3	A2	anode 2		sym125
mb	К	mounting base; cathode		
			TO-247 (SOT429)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BYV74W-400	TO-247	plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3 lead TO-247	SOT429		

# 7. Marking

Table 4. Marking codes

Type number	Marking code
BYV74W-400	BYV74W-400

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	400	V
V <sub>RWM</sub>	crest working reverse voltage		-	400	V
V <sub>R</sub>	reverse voltage	T <sub>mb</sub> ≤ 136 °C; DC	-	400	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 104 °C; square-wave pulse; per diode; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	15	A
I <sub>O(AV)</sub>	average output current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 94 °C; square-wave pulse; both diodes conducting	-	30	А

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Symbol	Parameter	Conditions	Min	Max	Unit
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	-	170	А
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	-	185	Α
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	150	°C

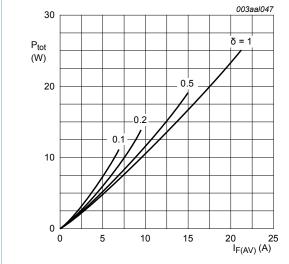


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; per diode; maximum values

$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_{O} &= 0.959 \text{ V; } R_{S} = 0.010 \text{ } \Omega \end{split}$$

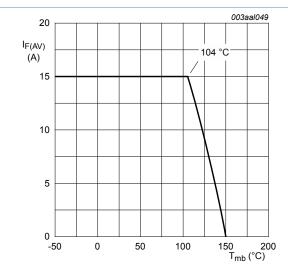


Fig. 3. Average forward current as a function of mounting base temperature; per diode; maximum values

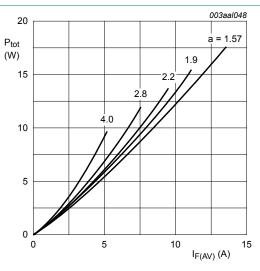


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; per diode; maximum values

a = form factor = 
$$I_{F(RMS)}/I_{F(AV)}$$
  
 $V_{O}$  = 0.959 V;  $R_{S}$  = 0.010  $\Omega$ 

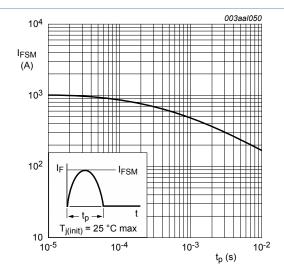


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; per diode; maximum values

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**Dual ultrafast power diode** 

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to	with heatsink compound; per diode; Fig. 5	-	-	2.4	K/W
	mounting base	with heatsink compound; both diodes conducting	-	-	1.4	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	_	45	-	K/W

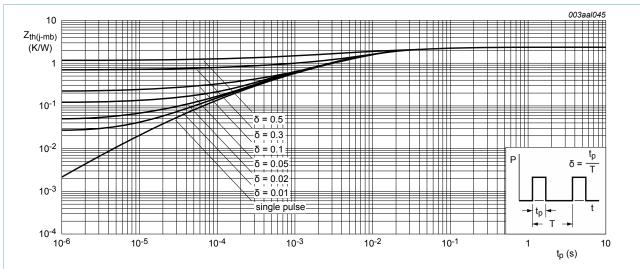


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse width; per diode; maximum values

## 10. Characteristics

### Table 7. Characteristics

characteristics are per diode unless otherwise stated

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static characteristics							
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	1.08	1.25	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	1.15	1.36	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	0.95	1.12	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 400 V; T <sub>j</sub> = 25 °C		-	10	50	μA
		V <sub>R</sub> = 400 V; T <sub>j</sub> = 100 °C		-	0.3	8.0	mA

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Dynamic characteristics								
Q <sub>r</sub>	recovered charge	$I_F = 2 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 20 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7		-	40	60	nC	
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/µs}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7		-	35	60	ns	
I <sub>RM</sub>	peak reverse recovery current	$I_F = 10 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 50 \text{ A/µs}$ ; $T_j = 100 \text{ °C}$ ; Fig. 7		-	4.2	5.2	A	
$V_{FRM}$	forward recovery voltage	$I_F = 10 \text{ A}$ ; $dI_F/dt = 10 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 8		-	2.5	-	V	

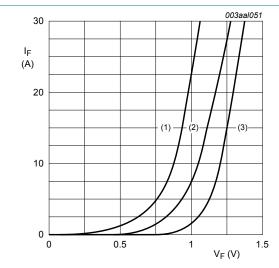


Fig. 6. Forward current as a function of forward voltage; per diode

(1)  $T_j = 150$  °C; typical values;

(2)  $T_j = 150$  °C; maximum values;

(3)  $T_j = 25$  °C; maximum values;  $V_O = 0.959 \text{ V}; R_S = 0.010 \Omega$ 

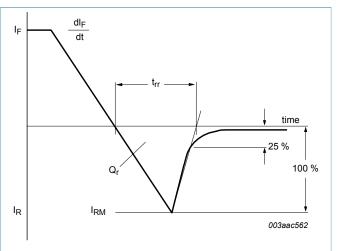
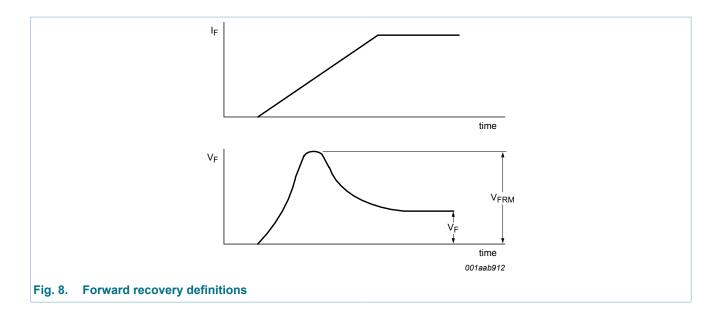


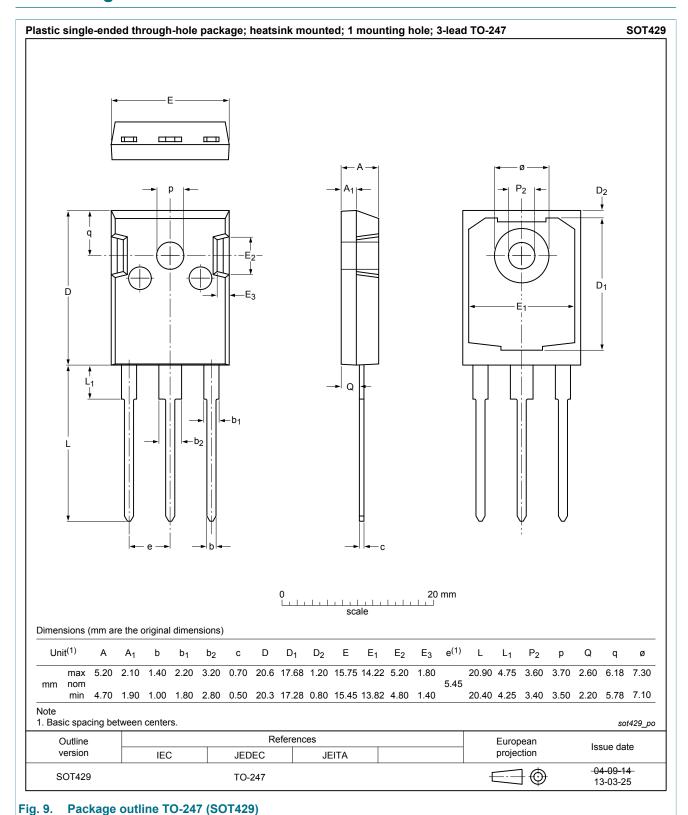
Fig. 7. Reverse recovery definitions; ramp recovery

## **Dual ultrafast power diode**



**Dual ultrafast power diode** 

## 11. Package outline



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#### **Dual ultrafast power diode**

## 12. Legal information

### 12.1 Data sheet status

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